

Bidirectional Low Capacitance TVSarray ™

APPEARANCE

SO-8

## DESCRIPTION

This Transient Voltage Suppressor (TVS) array is packaged in an SO-8 configuration giving protection to 2 Bidirectional data or interface lines. It is designed for use in applications where very low capacitance protection is required at the board level from voltage transients caused by electrostatic discharge (ESD) as defined in IEC 61000-4-2, electrical fast transients (EFT) per IEC 61000-4-4 and effects of secondary lightning. It is also available with either Tin-Lead plated terminations or as RoHS Compliant with annealed matte-Tin finish by adding an "e3" suffix to the part number\*.

Using the schematic on the second page, pins 1 & 2 are tied together for the first protected line, and pins 7 & 8 are tied together to the ground. The same would then occur for a second protected line where pins 3 & 4 are tied together and pins 5 & 6 are tied together to the ground. These may also be switched in polarity connections since the electrical features are the same in each antiparallel (opposite facing) leg when the pins are tied together in this manner for bidirectional protection.

These TVS arrays have a peak power rating of 500 watts for an 8/20  $\mu$ sec pulse. This array is suitable for protection of sensitive circuitry consisting of TTL, CMOS DRAM's, SRAM's, HCMOS, HSIC microprocessors, **UNIVERSAL SERIAL BUS (USB)** and I/O transceivers. The USB508XXC product provides board level protection from static electricity and other induced voltage surges that can damage or upset sensitive circuitry.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

#### FEATURES

- Protects up to 2 bidirectional lines
- Surge protection per IEC 61000-4-2, IEC 61000-4-4
- Provides electrically isolated protection
- UL 94V-0 Flamability Classification
- RoHS Compliant devices available by adding "e3" suffix
- ULTRA LOW CAPACITANCE 3 pF per line pair
- ULTRA LOW LEAKAGE

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# MAXIMUM RATINGS

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Peak Pulse Power: 500 watts (8/20 µs, Figure 1)
- Pulse Repetition Rate: < .01%</li>
- Solder Temperatures: 260°C for 10 s (maximum)

# ELECTRICAL CHARACTERISTICS

# osemi.com

**APPLICATIONS / BENEFITS** 

- EIA-RS485 data rates: 5 Mbs
- 10 Base T Ethernet
- USB date rate: 900 Mbs
- Tape & Reel per EIA Standard 481
- 13 inch reel; 2,500 pieces (OPTIONAL)
- Carrier tubes; 95 pcs (STANDARD)

## **MECHANICAL AND PACKAGING**

- Molded SO-8 Surface Mount
- Weight 0.066 grams (approximate)
- Marking: Logo, device marking code\*, date code
- Pin #1 defined by dot on top of package

ELECTRICAL CHARACTERISTICS									
PART NUMBER	DEVICE MARKING*	STANDOFF VOLTAGE V <sub>WM</sub> VOLTS	BREAKDOWN VOLTAGE V <sub>BR</sub> @1 mA VOLTS	CLAMPING VOLTAGE V <sub>c</sub> @ 1 Amp (Figure 2) VOLTS	CLAMPING VOLTAGE V <sub>c</sub> @ 5 Amp (Figure 2) VOLTS	STANDBY CURRENT I <sub>D</sub> @ V <sub>WM</sub> µA	CAPACITANCE (f=1 MHz) C @0V pF	$\begin{array}{c} \text{TEMPERATURE} \\ \text{COEFFICIENT} \\ \text{OF } V_{\text{BR}} \\ \alpha_{\text{VBR}} \\ \\ \text{mV/}^{\circ}\text{C} \end{array}$	
		MAX	MIN	MAX	MAX	MAX	MAX	MAX	
USB50803C	3C	3.3	4	8	11	200	3	-5	
USB50805C	5C	5.0	6.0	10.8	13	40	3	1	
USB50812C	12C	12.0	13.3	19	26	1	3	8	
USB50815C	15C	15.0	16.7	24	32	1	3	11	
USB50824C	24C	24.0	26.7	43	57	1	3	28	

Device marking has an e3 suffix added for the RoHS Compliant option, e.g. 3Ce3, 5Ce3, 12Ce3, 15Ce3, and 24Ce3.

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USB508xxC



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		SYMBOLS & DEFINITIONS						
	Symbol							
	V <sub>WM</sub>	Standoff Voltage: Maximum dc voltage that can be applied over the operating temperature range. V <sub>WM</sub> must be selected to be equal or be greater than the operating voltage of the line to be protected.						
	V <sub>BR</sub>	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current						
	Vc	Clamping Voltage: Maximum clamping voltage across the TVS device when subjected to a given current at a pulse time of 20 $\mu$ s.						
	ID	Standby Current: Leakage current at V <sub>WM.</sub>						
	С	Capacitance: Capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.						
7		GRAPHS						
	Ppp Peak Pulse Power (W)	B/20us 500W Pulse 8/20us 500W Pulse 100 100 100 100 100 100 100 10						

Figure 2 Pulse Wave Form

t -- Time in microsec

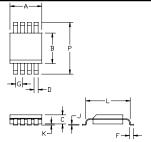


10

.1

# OUTLINE AND SCHEMATIC

10000



1

10

Figure 1

Peak Pulse Power Vs Pulse Time t = µsec

100

1000

DIM	INC	HES	MILLIMETERS		
DIN	MIN	MAX	MIN	MAX	
Α	0.188	0.197	4.77	5.00	
В	0.150	0.158 0.069 0.021	3.81 1.35 0.28	4.01	
С	0.053			1.75 0.53	
D	0.011				
F	0.0160	0.050	0.41	1.27	
G	0.050 BSC		1.27 BSC		
J	0.006	0.010	0.15	0.25	
K	0.004	0.008	0.10	0.20	
L	0.189	0.206	4.80	5.23	
Р	0.228	0.244	5.79	6.19	

## OUTLINE

